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(54) **Title:** PRECISE OXIDE DISSOLUTION

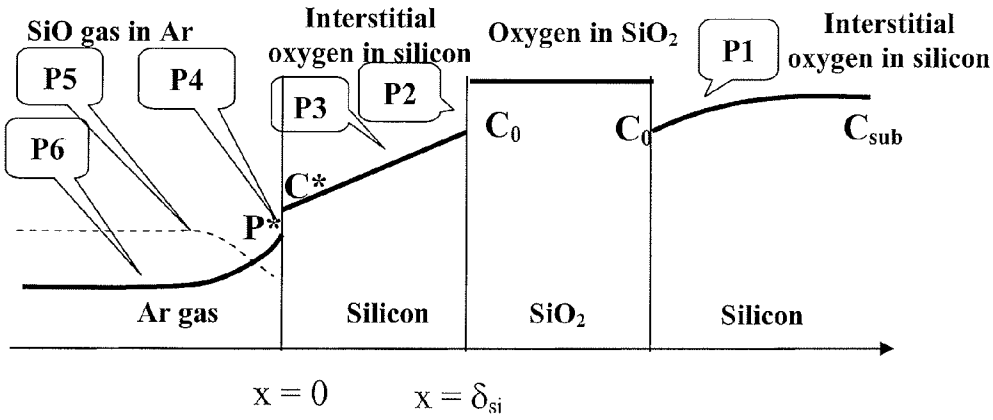


Figure 1

(57) **Abstract:** Method for dissolving the buried oxide layer of a SeOI wafer in order to decrease the thickness of said buried oxide layer, said SeOI wafer comprising: a thin working layer made from one or more semiconductor material(s); a support layer, and a buried oxide (BOX) layer between the working layer and the support layer, characterized in that the dissolution rate of the buried oxide layer is controlled and set to be below 0.06 Å/sec.

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